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ACCEPTED MANUSCRIPT

Anisotropic Growth Mechanism of Tungsten Diselenide Domains using Chemical Vapor Deposition Method

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Highlights

- WSe₂ domains were grown on sapphire substrate by chemical vapor deposition utilizing WO₃ and Se powders as precursors.
- WSe₂ domains was characterized by using Raman spectroscopy, PL, and AFM analysis.
- The kinetic energies of precursors strongly influenced the morphology and size of the WSe₂ domains formed during the growth process.
- Anisotropic morphogenesis and edge terminations of WSe₂ domains were investigated.

Abstract

Anisotropic transition metal dichalcogenide (TMDC) domains have stimulated a growing interest mainly due to their electronic properties that depend on the size, shape, and edge structures of the domains. In this work, we investigated the anisotropic morphogenesis and edge terminations of tungsten diselenide (WSe₂) domains grown on sapphire substrates by chemical vapor deposition (CVD) using tungsten oxide (WO₃) and selenium (Se) powders as

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